

WHAT IS CLAIMED IS:

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1. A semiconductor device, comprising:
a first conductive layer;
a first ball formed on said first conductive layer;
a second conductive layer arranged spaced apart from said first
conductive layer;
a second ball formed on said second conductive layer; and
a bonding wire connecting said first and second balls; wherein
said second ball is formed by mechanically deforming said bonding
wire.
2. The semiconductor device according to claim 1, wherein
said second ball is formed by bending said bonding wire on said
second conductive layer.
3. The semiconductor device according to claim 1, wherein
said second ball is formed by making said bonding wire curved on
said second conductive layer.
4. The semiconductor device according to claim 1, wherein
said first conductive layer includes an inner lead; and
said second conductive layer includes a bonding pad.
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5. The semiconductor device according to claim 1, comprising
a base;
a semiconductor element formed on said base with a die pad
interposed;
a sealing resin sealing said semiconductor element; and
an external terminal formed on a rear surface of said base; wherein
said first conductive layer includes a land formed on said base, and
said second conductive layer includes a bonding pad formed on said
semiconductor element.

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said step of mechanically deforming said bonding wire includes the step of making said bonding wire curved on said second conductive layer.

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10. The method of manufacturing a semiconductor device according to claim 7, wherein

said bonding wire is held by a bonding tool; and

5 said step of mechanically deforming said bonding wire includes the step of mechanically deforming said bonding wire on said second conductive layer by moving said bonding tool with said bonding wire being joined to said second conductive layer.

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